Supplementary Information

Surface engineering of nanoflower-like MoS₂ decorated porous Si₃N₄ ceramics for electromagnetic wave absorption

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Materials and Characterization

Materials

Commercial Si₃N₄ powder was used as starting material. Y_2O_3 and Al_2O_3 were used as sintering additives. Mono-dispersed poly methyl methacrylate (PMMA, $d_{50}=\sim30 \ \mu\text{m}$) micro-balls were used as a pore-forming agent. Sodium molybdate dihydrate (Na₂MoO₄·2H₂O) and thioacetamide (C₂H₅NS) were used for the synthesis of MoS₂. All chemicals were of analytical grade and were used as received without further purification.

Characterization

The phase composition of the samples was analyzed via X-ray diffraction (XRD, Cu K α as radiation, Germany). The morphology of the fracture surface was observed using field emission scanning electron microscope (SEM, Hitachi SU8220, Japan) and transmission electron microscopy (TEM, JEM-2100F). Apparent porosity was measured by the Archimedes method. The surface element composition and its chemical states were determined by X-ray photoelectron spectroscopy (XPS, Thermo Fisher Scientific ESCALAB 250). Raman spectra were obtained on a LabRam HR800 with a visible laser (532 nm) to characterize the structure of the samples. The vector network analyzer (VNA, Agilent E5071C; China) was carried out to test the complex permittivity of the samples with dimensions of 22.86 mm × 10.16 mm × 3 mm in the frequency range of 8.2-12.4 GHz.



Figure S1. The fracture surfaces of porous Si_3N_4 ceramic.



Figure S2. (a) The fracture surface and (b) EDS results of MoS_2/Si_3N_4 -1.70.



Figure S3. (a) The microstructure of initial Si_3N_4 powder. (b) XRD pattern of initial Si_3N_4 powder and porous Si_3N_4 ceramics.



Figure S4. (a) XPS survey spectrum and high resolution XPS spectra of (b) Mo 3d, (c)

S	2р,	(d)	Ν	1 <i>s</i>	,	and	(e)	Si	2p.

Sample	έ	ε"	$ an \delta_{arepsilon}$
MoS ₂ /Si ₃ N ₄ -0.70	3.52	0.92	0.26
MoS ₂ /Si ₃ N ₄ -1.05	3.82	1.94	0.51
MoS ₂ /Si ₃ N ₄ -1.40	4.64	2.69	0.58
MoS ₂ /Si ₃ N ₄ -1.75	5.72	3.64	0.64

Table S1. Summary of the average real part (ε) , imaginary part (ε) of complex permittivity, and dielectric loss tangent $(\tan \delta_{\varepsilon})$ for different samples